

NUP2125, SZNUP2125

Dual Line CAN Bus Protector

The SZ/NUP2125 has been designed to protect the CAN transceiver from ESD and other harmful transient voltage events. This device provides bidirectional protection for each data line with a single compact SC-70 (SOT-323) package, giving the system designer a low cost option for improving system reliability and meeting stringent EMI requirements.

Features

- 200 W Peak Power Dissipation per Line (8 x 20 μ sec Waveform)
- Diode Capacitance Matching
- Low Reverse Leakage Current (< 100 nA)
- IEC Compatibility:
 - IEC 61000-4-2 (ESD): Level 4
 - IEC 61000-4-4 (EFT): 50 A – 5/50 ns
 - IEC 61000-4-5 (Lighting) 3.0 A (8/20 μ s)
- ISO 7637-1, Nonrepetitive EMI Surge Pulse 2, 8.0 A (1 x 50 μ s)
- ISO 7637-3, Repetitive Electrical Fast Transient (EFT) EMI Surge Pulses, 50 A (5 x 50 ns)
- Flammability Rating UL 94 V-0
- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These are Pb-Free Devices

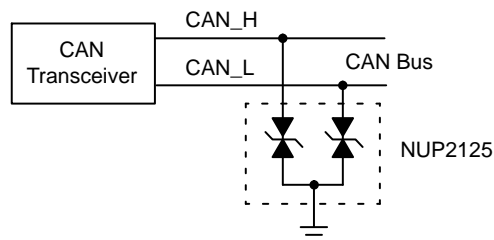
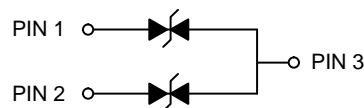
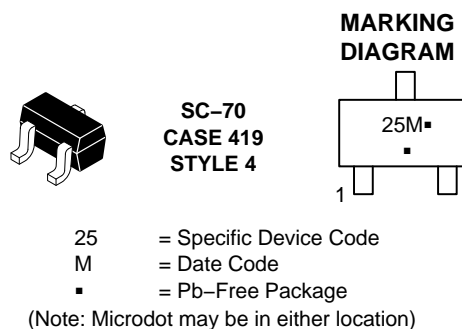
Applications

- Automotive Networks
 - ♦ CAN / CAN-FD
 - ♦ Low and High-Speed CAN
 - ♦ Fault Tolerant CAN



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ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

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MAXIMUM RATINGS (T_J = 25°C, unless otherwise specified)

Symbol	Rating	Value	Unit
PPK	Peak Power Dissipation, 8 x 20 μs Double Exponential Waveform (Note 1)	200	W
T _J	Operating Junction Temperature Range	–55 to 150	°C
T _J	Storage Temperature Range	–55 to 150	°C
T _L	Lead Solder Temperature (10 s)	260	°C
ESD	Human Body Model (HBM) Machine Model (MM) IEC 61000–4–2 Specification (Contact)	8.0 1.6 30	kV kV kV

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Non-repetitive current pulse per Figure 1.

ELECTRICAL CHARACTERISTICS (T_J = 25°C, unless otherwise specified)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V _{RWM}	Reverse Working Voltage	(Note 2)	24	–	–	V
V _{BR}	Breakdown Voltage	I _T = 1 mA (Note 3)	26.2	–	32	V
I _R	Reverse Leakage Current	V _{RWM} = 24 V	–	15	100	nA
V _C	Clamping Voltage	I _{PP} = 1 A (8 x 20 μs Waveform) (Note 4)	–	33.4	36.6	V
V _C	Clamping Voltage	I _{PP} = 3 A (8 x 20 μs Waveform) (Note 4)	–	44	50	V
I _{PP}	Maximum Peak Pulse Current	8 x 20 μs Waveform (Note 4)	–	–	3.0	A
C _J	Capacitance	V _R = 0 V, f = 1 MHz (Line to GND)	–	–	10	pF
ΔC	Diode Capacitance Matching	V _R = 0 V, 5 MHz (Note 5)	–	0.26	2	%

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- TVS devices are normally selected according to the working peak reverse voltage (V_{RWM}), which should be equal or greater than the DC or continuous peak operating voltage level.
- V_{BR} is measured at pulse test current I_T.
- Pulse waveform per Figure 1.
- ΔC is the percentage difference between C_J of lines 1 and 2 measured according to the test conditions given in the electrical characteristics table.

ORDERING INFORMATION

Device	Package	Shipping [†]
NUP2125WTT1G	SC–70 (Pb–Free)	3000 / Tape & Reel
SZNUP2125WTT1G	SC–70 (Pb–Free)	3000 / Tape & Reel
NUP2125WTT3G	SC–70 (Pb–Free)	10000 / Tape & Reel
SZNUP2125WTT3G	SC–70 (Pb–Free)	10000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TYPICAL PERFORMANCE CURVES

($T_J = 25^\circ\text{C}$ unless otherwise noted)

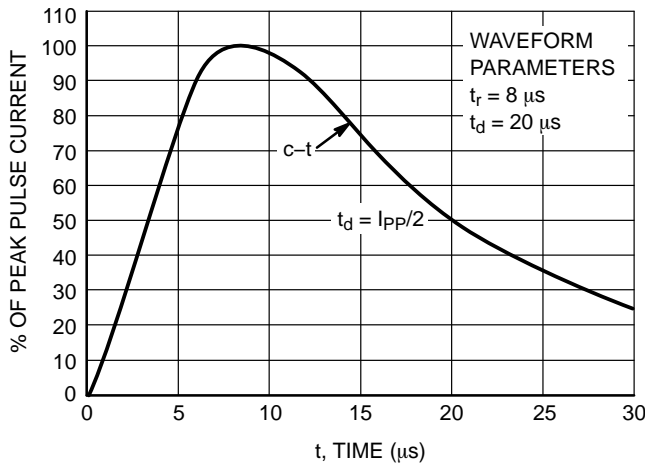


Figure 1. Pulse Waveform, $8 \times 20 \mu\text{s}$

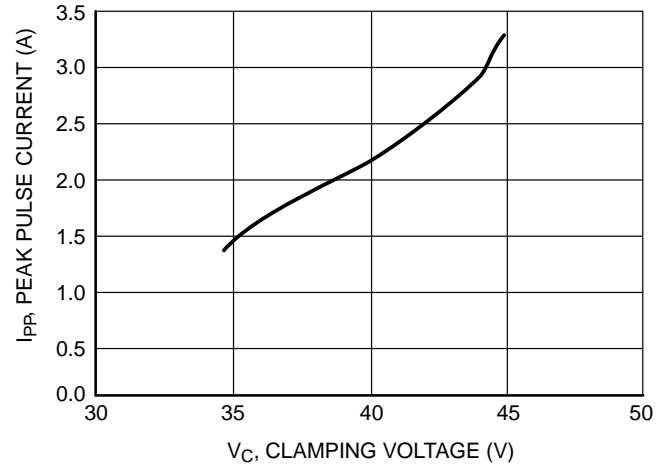


Figure 2. Clamping Voltage vs Peak Pulse Current

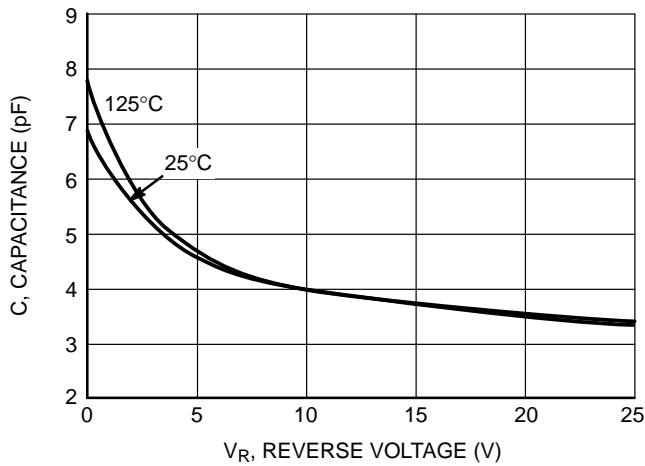


Figure 3. Typical Junction Capacitance vs Reverse Voltage

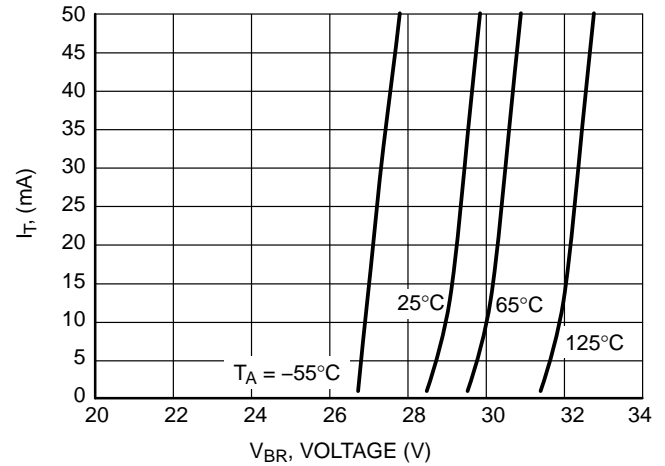


Figure 4. V_{BR} versus I_T Characteristics

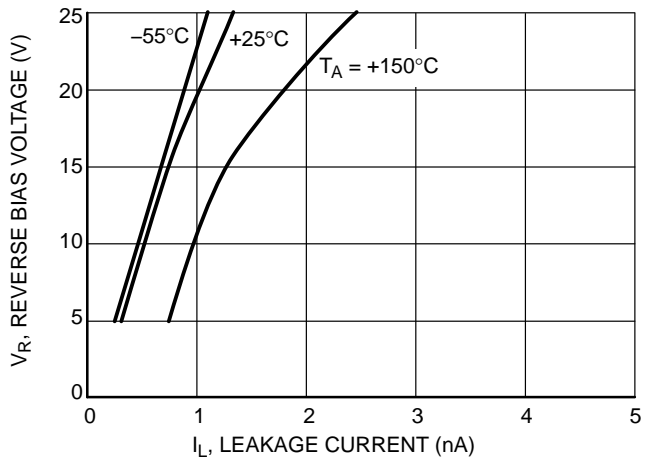


Figure 5. I_R versus Temperature Characteristics

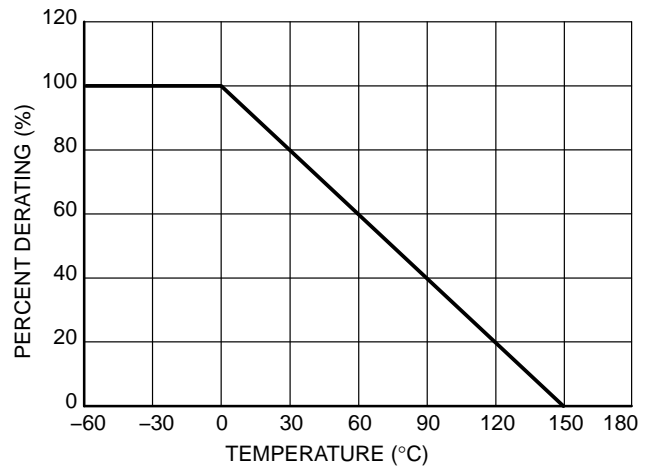
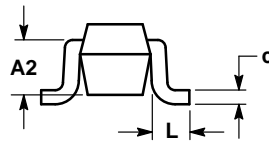
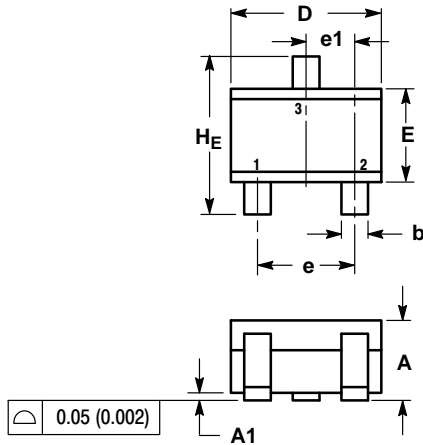


Figure 6. Temperature Power Dissipation Derating

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PACKAGE DIMENSIONS

SC-70 (SOT-323) CASE 419-04 ISSUE N



NOTES:

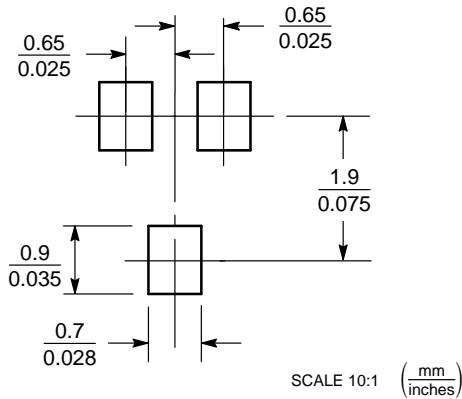
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 REF		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095

STYLE 4:


- PIN 1: CATHODE
- CATHODE
- ANODE

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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